### **Vishay Semiconductors**

Hyperfast Rectifier, 1 A FRED Pt<sup>®</sup>



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DESIGN SUPPORT TOOLS [click logo to get started.



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	1 A					
V <sub>R</sub>	200 V					
V <sub>F</sub> at I <sub>F</sub> (typ. 125 °C)	0.74 V					
t <sub>rr</sub>	25 ns					
T <sub>J</sub> max.	175 °C					
Package	SMF (DO-219AB)					
Circuit configuration	Single					

#### FEATURES

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V			
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	А			
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	35	A			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage V <sub>F</sub>	V	I <sub>F</sub> = 1 A	-	0.87	0.93	V
	۷F	I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C	-	0.74	0.8	
Devenue la clue de comment			-	-	2	
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	0.5	8	μA
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	5	-	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-		
Powerze receiver time		$I_{\rm F} = 0.5 \; {\rm A}, \; I_{\rm R} = 1 \; {\rm A}, \; I_{\rm rr}$	-	-	25			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	ns	
		T <sub>J</sub> = 125 °C		-	23	-		
		T <sub>J</sub> = 25 °C	$I_F = 1 A$	-	1.6	-	Α	
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 160 V	-	2.5	-	~	
D	0	T <sub>J</sub> = 25 °C		-	13	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	30	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	+175	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W	
Approvimate weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		М	DH		

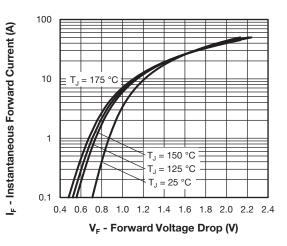


Fig. 1 - Typical Forward Voltage Drop Characteristics

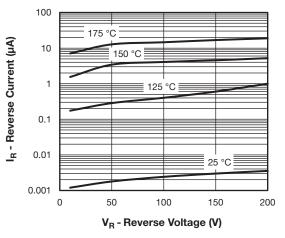
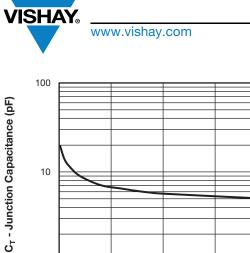


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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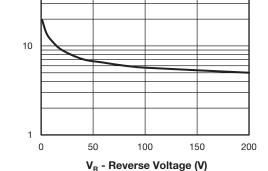


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

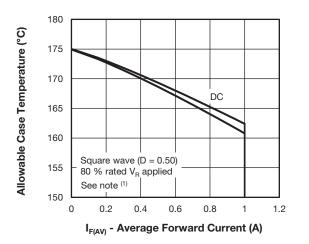


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

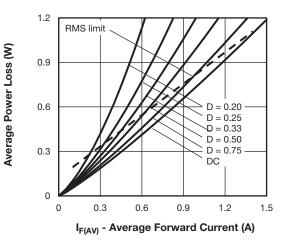
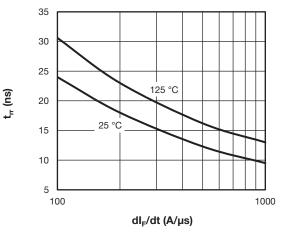


Fig. 5 - Forward Power Loss Characteristics





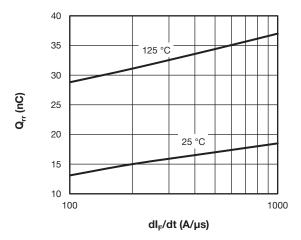


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

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## VS-1EFH02HM3

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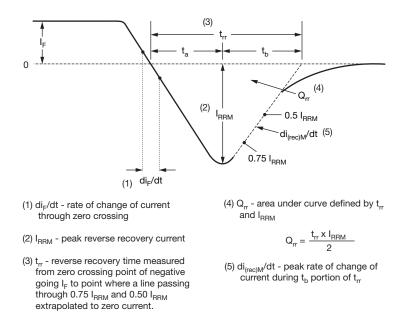


Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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Device code	VS-	1	E	F	н	02	н	М3
		2	3	4	5	6	7	8
	1		hay Sen rrent rat			oduct		
	3		cuit con single d	•	n:			
	4	- F=	SMF pa	ackage				
	5		cess ty hyperfa		very			
	6	- Vol	tage co	de (02 =	200 V)			
	7		= AEC-G					
	8	- M3	= halog	jen-free,	, RoHS-	complia	ant, and	termin

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-1EFH02HM3/I	10 000	10 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95572						
Part marking information	www.vishay.com/doc?95618					
Packaging information	www.vishay.com/doc?95577					
SPICE model	www.vishay.com/doc?96012					
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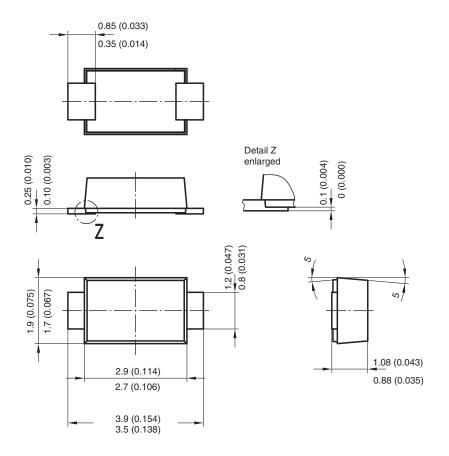
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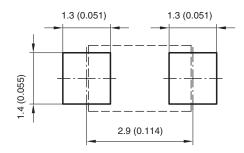
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## SMF (DO-219AB)

#### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



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